

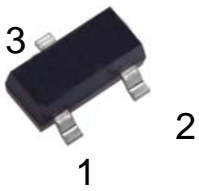


SOT-23 Plastic-Encapsulate Transistors

<p style="text-align: center;"></p> <p>MMBT3906</p> <p>Features:</p> <p><input type="checkbox"/> PNP Transistor</p> <p><input type="checkbox"/> Complementary to MMBT3904</p> <p>Marking:2A</p>	<p style="text-align: center;">SOT-23</p> <p style="text-align: right;"></p> <p style="text-align: center;"></p> <p style="text-align: right;">1.Base (B) 2. Emitter (E) 3. Collector (C)</p>
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MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.2	A
P _C	Collector Dissipation	0.2	W
R _{θJA}	Thermal resistance junction to ambient	625	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

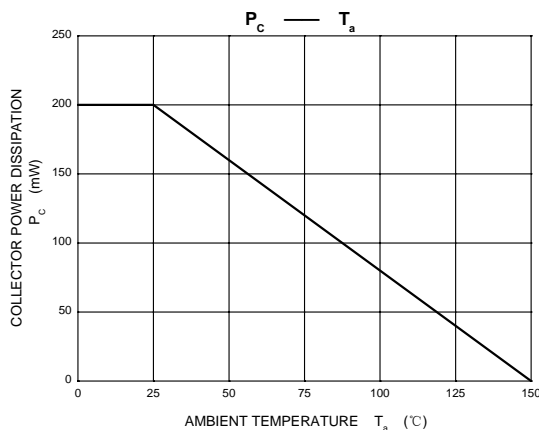
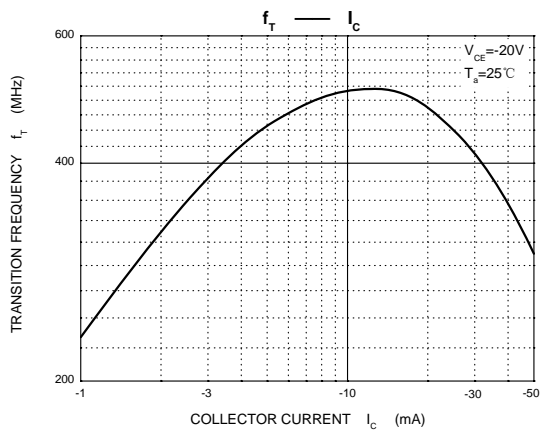
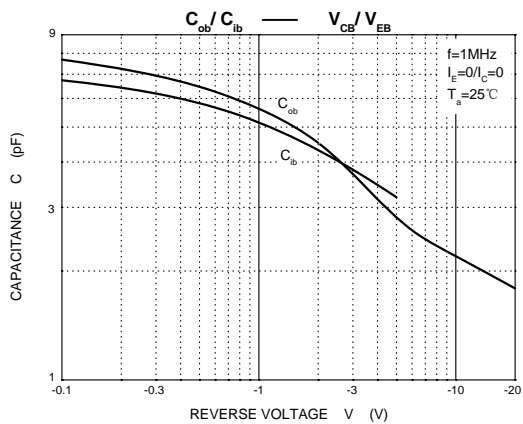
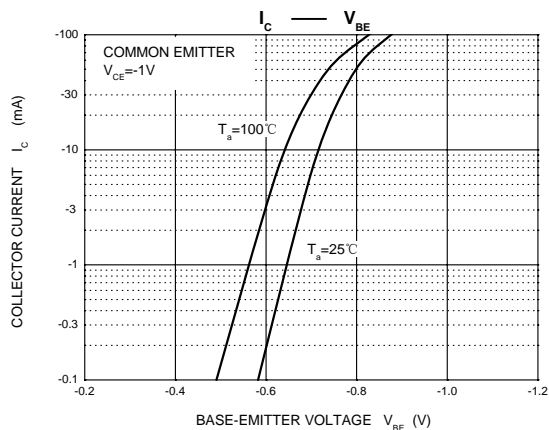
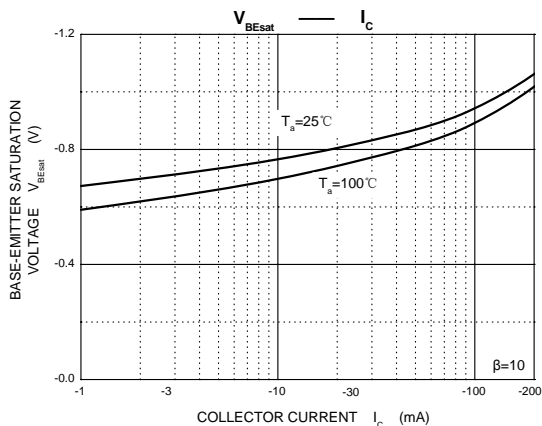
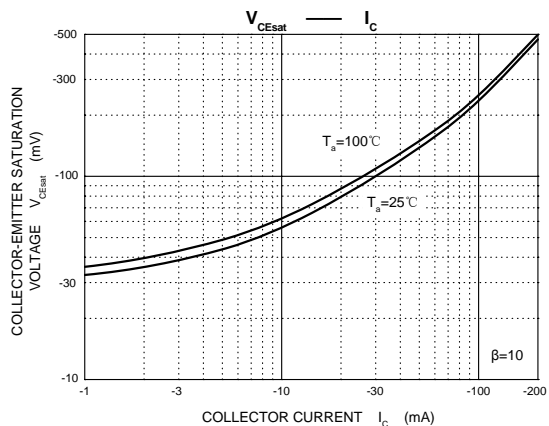
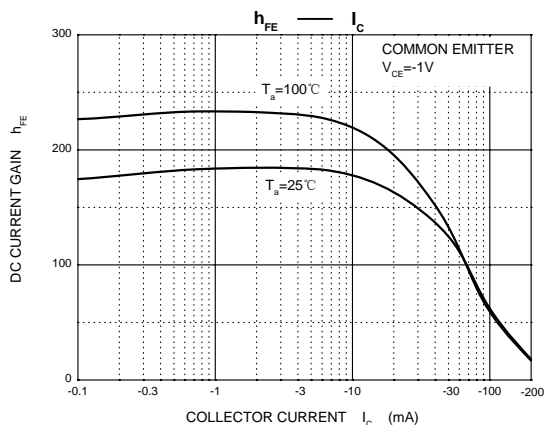
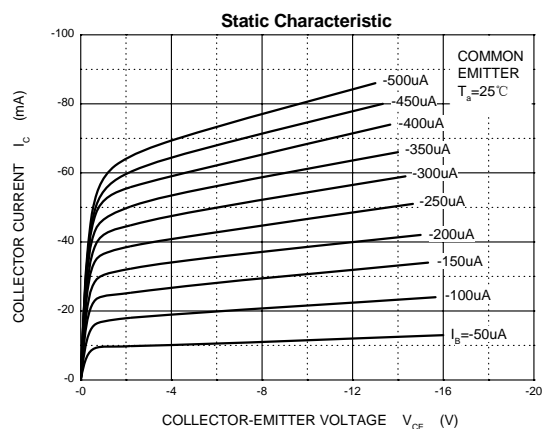
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-40		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B =0	-40		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} = -40 V, I _E =0		-100	nA
Collector cut-off current	I _{CEX}	V _{CE} =-30V, V _{BE(off)} =-3V		-50	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0		-100	nA
DC current gain	h _{FE1}	V _{CE} =-1V, I _C = -10mA	100	300	
	h _{FE2}	V _{CE} = -1V, I _C =-50mA	60		
	h _{FE3}	V _{CE} = -2V, I _C =-100mA	30		
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =-50mA, I _B =-5mA		-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -50mA, I _B =-5mA		-0.95	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	300		MHz
Delay Time	t _d	V _{CC} =-3V, V _{BE} =-0.5V		35	nS
Rise Time	t _r	I _C =-10mA, I _{B1} =I _{B2} =-1mA		35	nS
Storage Time	t _s	V _{CC} =-3V, I _C =-10mA		225	nS
Fall Time	t _f	I _{B1} =I _{B2} =-1mA		75	nS

CLASSIFICATION OF h_{FE(1)}

HFE	100-300	
RANK	L	H
RANGE	100 - 200	200 - 300

SOT-23 Plastic-Encapsulate Transistors

Typical Characteristics



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